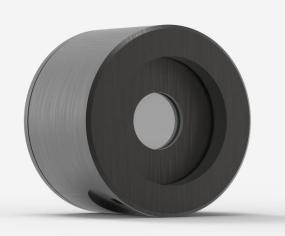




PE10B-SI-D0

Photodiode detector for laser energy measurement up to 81 nJ.



PRODUCT FAMILY KEY FEATURES

VERY LOW NOISE LEVEL

Take measurements with a noise level as low as 8 fJ (model PE3B-Si only) with the M-LINK, MAESTRO and S-LINK monitors.

3 SENSORS AVAILABLE

- $\bullet~$ PE-B-SI family: 3 and 10 mm Ø silicon sensors for 0.21 to 1.08 μm
- \bullet PE5B-GE: 5 mm Ø, germanium sensor for 0.8 to 1.65 μm
- $\bullet~$ PE3B-IN: 3 mm Ø, InGaAs sensor for 0.9 to 1.7 μm

SMART INTERFACE

Containing all the calibration data

COMPATIBLE STAND

STAND-D-233

SPECIFICATIONS

MEASUREMENT CAPABILITIES
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Spectral range ¹	210 - 1080 nm
Typical rise time	30 µs
Maximum repetition frequency	1000 Hz
Maximum measurable energy ²	81 nJ
Noise equivalent energy ³	1.5 pJ
Maximum pulse width	10 μs
Energy calibration uncertainty	±18 % (210 - 229 nm) ±8.0 % (230 - 254 nm) ±6.5 % (255 - 399 nm) ±2.5 % (400 - 899 nm) ±4.0 % (900 - 1009 nm) ±7.5 % (1010 - 1080 nm)

- 1. This detector is NIST-traceable at the calibration wavelength of 634 nm. Typical values are used at other wavelengths.
- 2. At 634 nm. See curves for maximum power at other wavelengths.
- 3. Nominal value. Actual value depends on environmental electromagnetic interference and wavelength.

DAMAGE THRESHOLDS

Maximum average power density	65 mW/cm ²
Maximum energy density	5 μJ/cm²
Maximum power	230 μW
DUVSICAL CHADACTEDISTICS	

PHYSICAL CHARACTERISTICS	
Aperture diameter	10 mm
Absorber	SiUV
Dimensions	38.1Ø x 27.4D mm
Weight	0.09 kg
Distance to sensor face	13.7 mm

ORDERING INFORMATION

PE10B-Si-IDR-D0

PE10B-Si-D0	202019



PE10B-Si-INE-D0

PEIOB-SI-INT-DO 202651

Specifications are subject to change without notice. Refer to the user manual for complete specifications.

INTERESTED IN THIS PRODUCT?

GET A QUOTE

Find your local sales representative at gentec-eo.com/contact-us